BUL416

Symbol	Parameter	Value	Unit	
T_J	Max. Operating Junction Temperature	150	°C	

Table 3: Thermal Data

R _{thj-case}	Thermal Resistance Junction-Case	Max	1.14	°C/W
R _{thj-amb}	Thermal Resistance Junction-Ambient	Max	62.5	°C/W

Table 4: Electrical Characteristics ($T_{case} = 25$ °C unless otherwise specified)

Symbol	Parameter	Test C	onditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current	V _{CE} = 1600 V				100	μΑ
	(V _{BE} =0 V)	V _{CE} = 1600 V	T _j = 125 °C			500	μA
I _{CEO}	Collector Cut-off Current	V _{CE} = 800 V				≥50	μA
	(I _B = 0)						
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage	I _C = 100 mA	L = 25 mH	800	DO	1.0	V
	$(I_B = 0)$					4/5	וכ
V _{EBO}	Emitter-Base Voltage	I _E = 10 mA	- 40	9	1	0,,,	V
	$(I_C = 0)$		76,		70		
V _{CE(sat)} *	Collector-Emitter	I _C = 2 A	I _B = 0.4 A	740		1.5	V
	Saturation Voltage	I _C = 4 A	$I_B = 1.33 \text{ A}$			3	V
V _{BE(sat)} *	Base-Emitter Saturation	I _C = 2 A	I _B = 0.4 A			1.2	V
	Voltage	I _C = 4 A	I _B = 1.33 A			1.5	V
h _{FE} *	DC Current Gain	I _C = 10 mA	V _{CE} = 5 V	10			
		! _C - 0.7 A	$V_{CE} = 5 V$				
	41)	Group A) (12		27	
	00,0	Group B		25		40	
	INDUCTIVE CAD	I _C = 3 A	I _{B1} = 1 A				
t _s	Storage ime	$V_{BE(off)} = -5 V$	$R_{BB} = 0 \Omega$		2.3		μs
t _f	i al'ii ne	V _{clamp} = 200 V	L = 200 µH		650		ns
	200	(see figure 12)					
20,	INDUCTIVE LOAD	I _C = 3 A	I _{B1} = 1 A				
t _s	Storage Time	$V_{BE(off)} = -5 V$	$R_{BB} = 0 \Omega$		3		μs
t _f	Fall Time	V _{clamp} = 200 V	L = 200 µH		680		ns
		T _j = 100 °C	(see figure 12)				

^{*} Pulsed: Pulsed duration = 300 μ s, duty cycle \leq 1.5 %.

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[#] Note: Product is pre-selected in DC current gain (Group A and Group B). STMicroelectronics reserves the right to ship either groups according to production availability. Please contact your nearest STMicroelectronics sales office for delivery datails.

Figure 3: Safe Operating Area

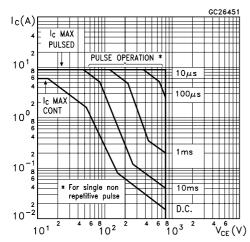


Figure 4: DC Current Gain

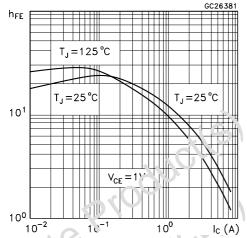


Figure 5: Collector-Emitter Saturation Voltage

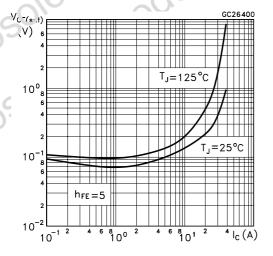


Figure 6: Derating Curve

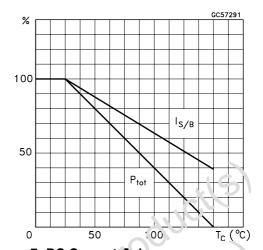


Figure 7: DC Current Gain

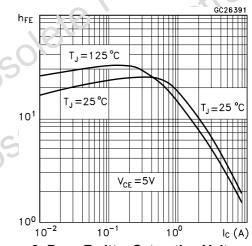
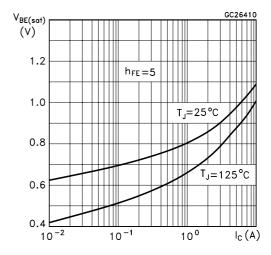


Figure 8: Base-Emitter Saturation Voltage



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Figure 9: Inductive Load Fall Time

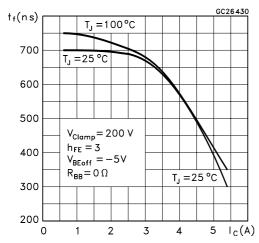


Figure 10: Reverse Biased SOA

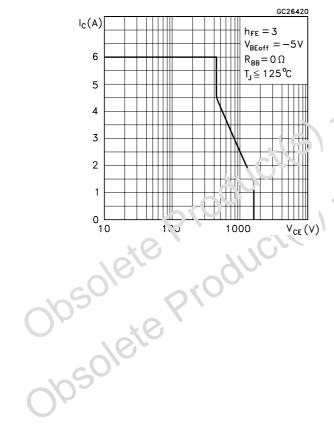
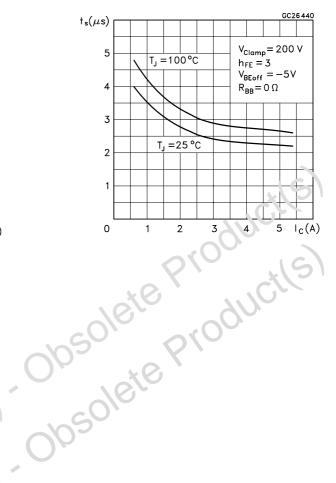


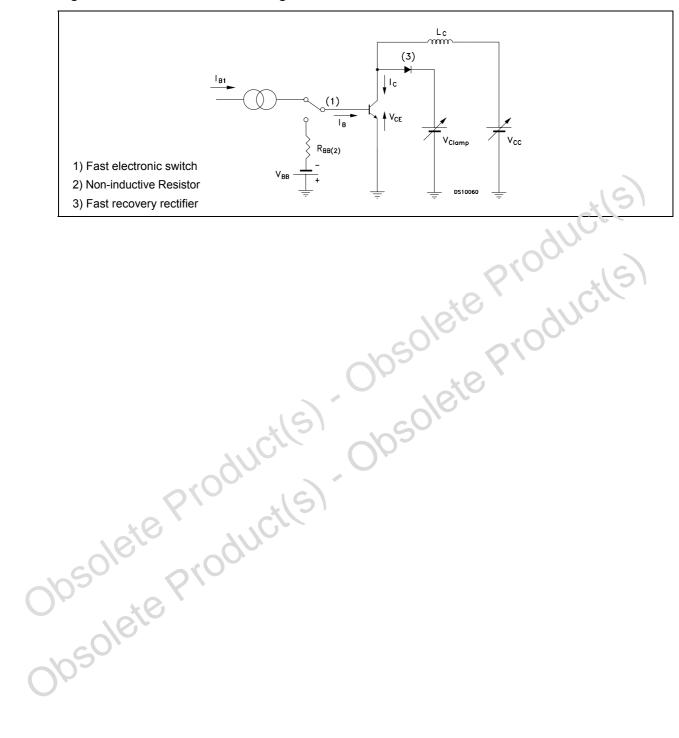
Figure 11: Resistive Load Stoarage Time



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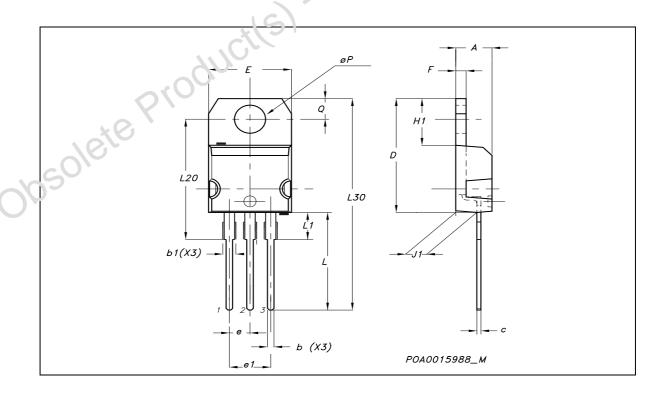
Figure 12: Inductive Load Switching Test Circuit



A7/.

TO-220 MECHANICAL DATA

DIM.	mm.			inch			
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
Α	4.40		4.60	0.173		0.181	
b	0.61		0.88	0.024		0.034	
b1	1.15		1.70	0.045		0.066	
С	0.49		0.70	0.019		0.027	
D	15.25		15.75	0.60		0.620	
E	10		10.40	0.393		0.400	
е	2.40		2.70	0.094		€ 106	
e1	4.95		5.15	0.194	1.1	0.202	
F	1.23		1.32	0.048		0.052	
H1	6.20		6.60	0.244		0.256	
J1	2.40		2.72	0.094		0.107	
L	13		14	0.511		0.551	
L1	3.50		3.93	0.137		0.154	
L20		16.40		18	0.645		
L30		28.90		0/	1.137		
øΡ	3.75		3.85	0.147		0.151	
Q	2.65		2.55	0.104		0.116	



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Table 5:

Version	Release Date	Change Designator
14-Jan-2004	1	First Release.
09-Sep-2004	2	Second Release.
26-Jan-2005	3	Third Release.

Obsolete Product(s) Obsolete Product(s)
Obsolete Product(s)
Obsolete Product(s)

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